

# isc Silicon PNP Power Transistor

# 2SB1231

### DESCRIPTION

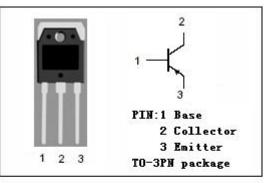
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -100V(Min)
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD1841
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

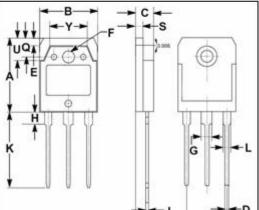
## **APPLICATIONS**

• Designed for motor drivers, converters and other general High-current switching applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-110	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
Ιc	Collector Current-Continuous	-25	A	
I <sub>CP</sub>	Collector Current-Pulse	-40	А	
I <sub>B</sub>	Base Current-Continuous	-8	А	
Pc	Collector Power Dissipation @ $T_a=25^{\circ}C$	3	- w	
	Collector Power Dissipation @ $T_c$ =25 °C	120		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





R

	m	mm	
DIM	MIN	MAX	
Α	19.60	20.10	
В	15.50	15.70	
С	4.70	4.90	
D	0.90	1.10	
E	1.90	2.10	
F	3.40	3.60	
G	2.90	3.20	
Н	3.20	3.40	
J	0.595	0.605	
Κ	20.00	20.70	
L	1.90	2.20	
Ν	10.89	10.91	
Q	4.90	5.10	
R	3.35	3.45	
S	1.995	2.100	
U	5.90	6.10	
Y	9.90	10.10	

isc website: www.iscsemi.com



# isc Silicon PNP Power Transistor

# 2SB1231

# ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	Ic= -5mA ; R <sub>BE</sub> =∞	-100			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>E</sub> = 0	-110			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10Α; I <sub>B</sub> = -1Α			-0.8	V
$V_{\text{BE}(\text{sat})}$	Base -Emitter Saturation Voltage	Ic= -10A; I <sub>B</sub> = -1Α			-1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-100	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-100	μA
hfe-1	DC Current Gain	I <sub>C</sub> = -2.5A; V <sub>CE</sub> = -2V	50		140	
hfe-2	DC Current Gain	Ic= -10A; Vce= -2V	20			

### h<sub>FE-1</sub> Classifications

Р	Q	
50-100	70-140	

## NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.